

Product Summary

The GESDBN24VD32 is designed to protect voltage sensitive electronic components from ESD and other transients. Excellent clamping capability, low leakage, low capacitance, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in digital cameras, cellular phones, MP3 players and many other portable applications where board space is at a premium.

Feature

- Low reverse stand-off voltage: 24V Max.
- Low reverse clamping voltage
- Ultra-low leakage current
- Fast response time
- IEC 61000-4-2 Level 4 ESD protection

Application

- Digital cameras
- Portable applications
- Audio and video equipment
- USB Interface
- Mobile phone

Marking:

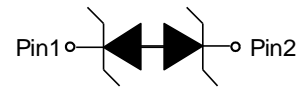


Front Side
24M=Device Code

SOD-323



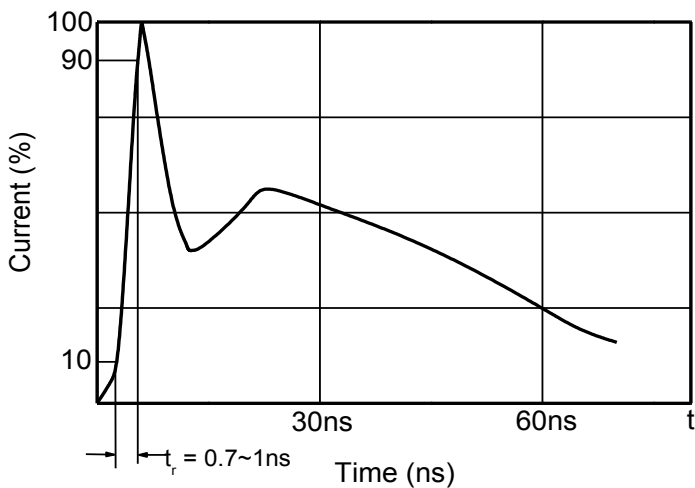
Schematic diagram



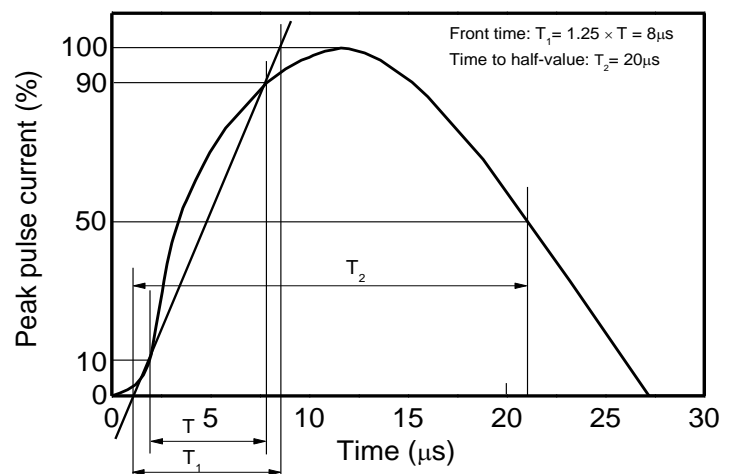
Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
IEC 61000-4-2 ESD Voltage	Air Model	±30	kV
IEC 61000-4-2 ESD Voltage	Contact Model	±30	
JESD22-A114-B ESD Voltage	Per Human Body Model	±16	
ESD Voltage	Machine Model	±0.4	
Peak Pulse Power (8/20μs)	P _{pk}	480	W
Peak Pulse Current (8/20μs)	I _{PP}	9	A
Junction Temperature	T _J	-55~ +125	°C
Storage Temperature	T _{stg}	-55~ +150	°C

Contact discharge current waveform per IEC61000-4-2

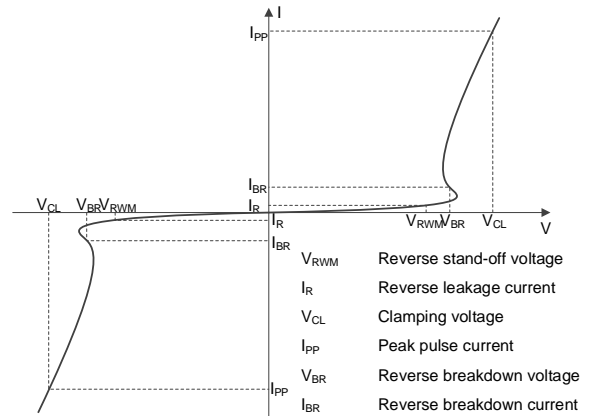


8/20μs waveform per IEC61000-4-5



Electrical Parameter

Symbol	Parameter
V _C	Clamping Voltage @ I _{PP}
I _{PP}	Peak Pulse Current
V _{BR}	Breakdown Voltage @ I _{BR}
I _{BR}	Test Current
I _R	Reverse Leakage Current @ V _{RWM}
V _{RWM}	Reverse Standoff Voltage



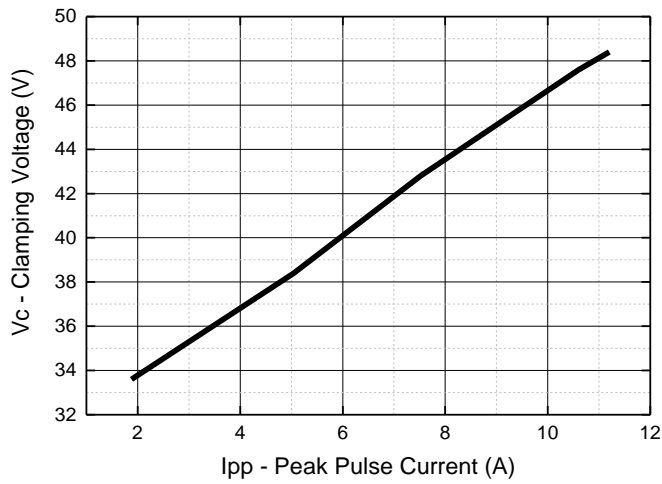
V-I characteristics for a Bi-directional TVS

Electrical Characteristics (T_a=25°C unless otherwise specified)

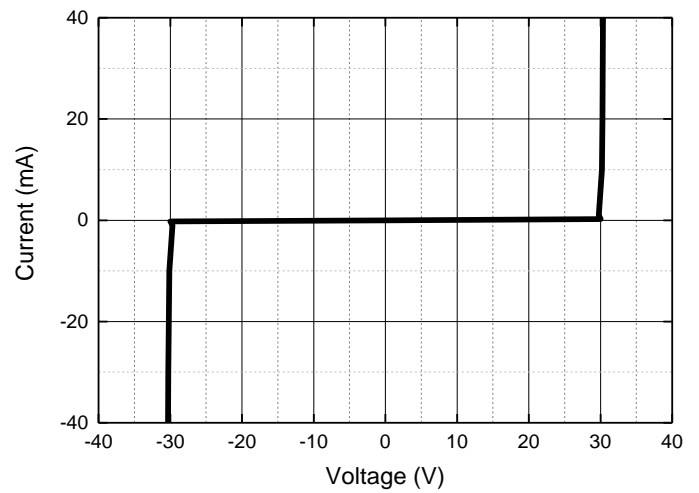
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse stand-off voltage	V _{RWM}				24	V
Reverse leakage current	I _R	V _{RWM} =24V			0.1	μA
Breakdown voltage	V _(BR)	I _T =1mA	26		32	V
Clamping voltage	V _{C1}	I _{PP} = 1A (8 x 20μs pulse)		32		V
	V _{C2}	I _{PP} = 9A (8 x 20μs pulse)		46		V
Junction capacitance	C _J	V _R =0V, f=1MHz		38	60	pF

Typical Characteristics

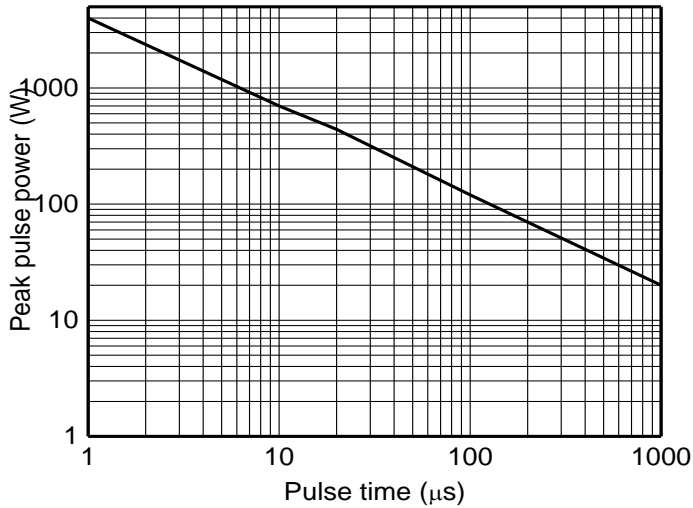
V_C vs. I_{PP}



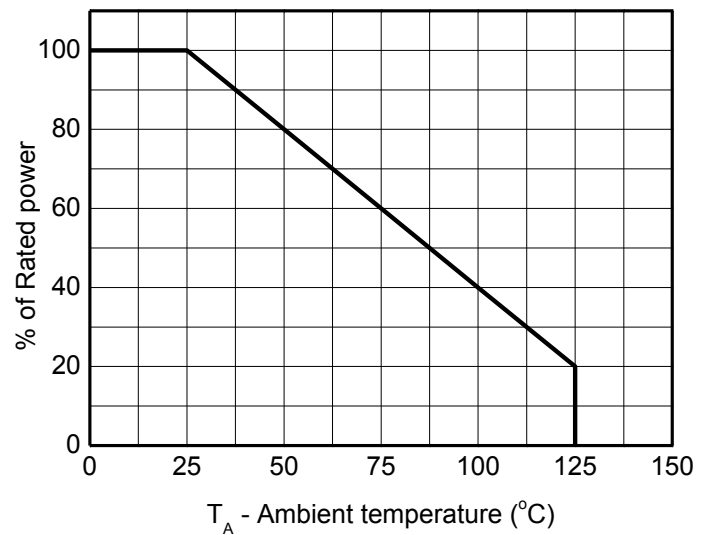
I-V Curve

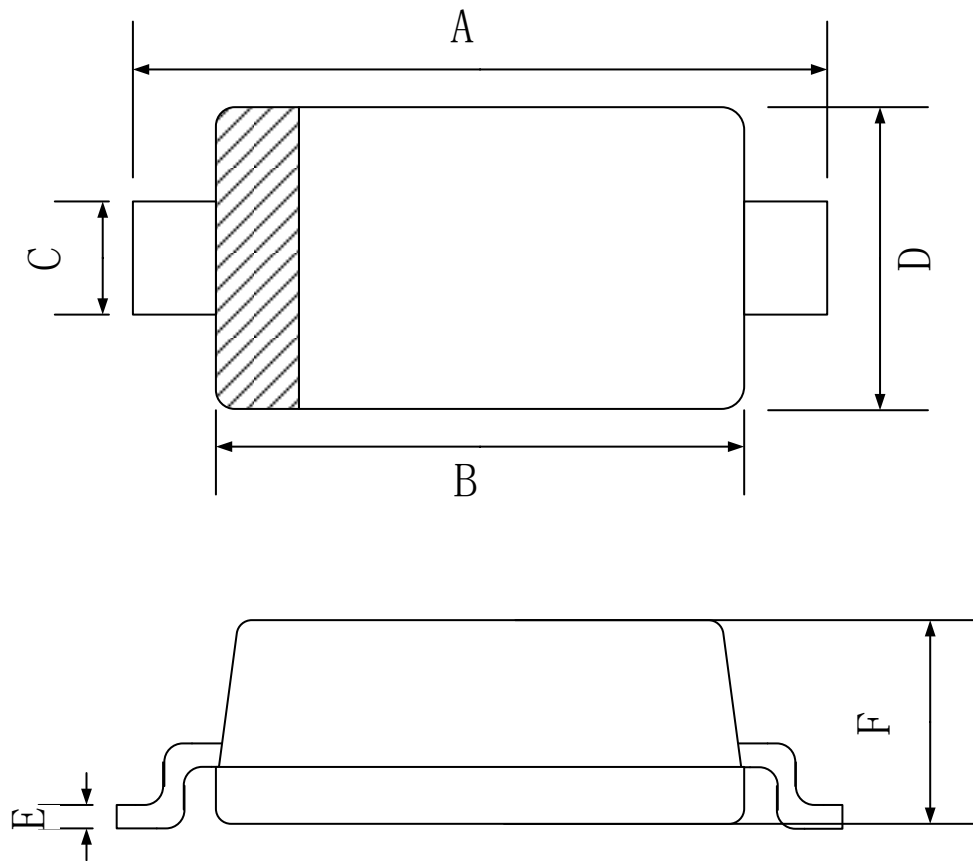


Peak pulse power vs. Pulse time



Power derating vs. Ambient temperature



SOD-323 Package Outline Dimensions


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	2.30	2.50	2.70
B	1.60	1.70	1.90
C	0.25	0.325	0.40
D	1.15	1.25	1.35
E	0.089	0.095	0.101
F	0.80	0.90	1.00

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)